



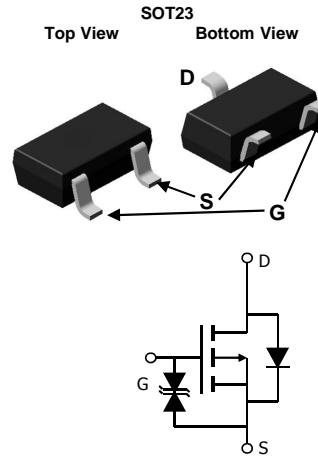
General Description

The AO3415 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch applications. ESD protected.

| | |
|-------------------------------------|--------|
| V_{DS} | -20V |
| I_D (at $V_{GS}=-4.5V$) | -4A |
| $R_{DS(ON)}$ (at $V_{GS} = -4.5V$) | < 41mΩ |
| $R_{DS(ON)}$ (at $V_{GS} = -2.5V$) | < 53mΩ |
| $R_{DS(ON)}$ (at $V_{GS} = -1.8V$) | < 65mΩ |

Applications

- Load Switch
- DC/DC Converter
- Switching Circuits
- LED Driver



Order Information

| Product | Package | Marking | Packing | Min Unit Quantity |
|---------|---------|---------|--------------|-------------------|
| AO3415 | SOT23 | 3415 | 3000PCS/Reel | 3000PCS |

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Maximum | Units |
|--|----------------|------------|-------|
| Drain-Source Voltage | V_{DS} | -20 | V |
| Gate-Source Voltage | V_{GS} | ± 8 | V |
| Continuous Drain Current ^A | I_D | -4 | A |
| $T_A=70^\circ\text{C}$ | | -3.5 | |
| Pulsed Drain Current ^C | I_{DM} | -30 | |
| Power Dissipation ^B | P_D | 1.5 | W |
| $T_A=25^\circ\text{C}$ | | 1 | |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | °C |

Thermal Characteristics

| Parameter | Symbol | Typ | Max | Units |
|---|-----------------|-----|-----|-------|
| Maximum Junction-to-Ambient ^A | $R_{\theta JA}$ | 65 | 80 | °C/W |
| Maximum Junction-to-Ambient ^{A,D} Steady-State | | 85 | 100 | °C/W |
| Maximum Junction-to-Lead | $R_{\theta JL}$ | 43 | 52 | °C/W |



Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|-----------------------------|---------------------------------------|--|------|-------|----------|------------------|
| STATIC PARAMETERS | | | | | | |
| BV_{DSS} | Drain-Source Breakdown Voltage | $I_D=-250\mu\text{A}, V_{GS}=0\text{V}$ | -20 | | | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS}=-20\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$ | | | -1 -5 | μA |
| I_{GSS} | Gate-Body leakage current | $V_{DS}=0\text{V}, V_{GS}= \pm 8\text{V}$ | | | ± 10 | μA |
| $V_{\text{GS(th)}}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}, I_D=-250\mu\text{A}$ | -0.3 | -0.57 | -0.9 | V |
| $I_{\text{D(ON)}}$ | On state drain current | $V_{GS}=-4.5\text{V}, V_{DS}=-5\text{V}$ | -30 | | | A |
| $R_{\text{DS(ON)}}$ | Static Drain-Source On-Resistance | $V_{GS}=-4.5\text{V}, I_D=-4\text{A}$ $T_J=125^\circ\text{C}$ | 34 | 41 | | $\text{m}\Omega$ |
| | | $V_{GS}=-2.5\text{V}, I_D=-4\text{A}$ | 49 | 59 | | $\text{m}\Omega$ |
| | | $V_{GS}=-1.8\text{V}, I_D=-2\text{A}$ | 42 | 53 | | $\text{m}\Omega$ |
| | | $V_{GS}=-1.5\text{V}, I_D=-1\text{A}$ | 52 | 65 | | $\text{m}\Omega$ |
| g_{FS} | Forward Transconductance | $V_{DS}=-5\text{V}, I_D=-4\text{A}$ | 61 | | | s |
| V_{SD} | Diode Forward Voltage | $I_S=-1\text{A}, V_{GS}=0\text{V}$ | 20 | | -0.64 | V |
| I_S | Maximum Body-Diode Continuous Current | | | | -1 | A |
| DYNAMIC PARAMETERS | | | | | | |
| C_{iss} | Input Capacitance | $V_{GS}=0\text{V}, V_{DS}=-10\text{V}, f=1\text{MHz}$ | 600 | 751 | 905 | pF |
| C_{oss} | Output Capacitance | | 80 | 115 | 150 | pF |
| C_{rss} | Reverse Transfer Capacitance | | 48 | 80 | 115 | pF |
| R_g | Gate resistance | $V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$ | 6 | 13 | 20 | Ω |
| SWITCHING PARAMETERS | | | | | | |
| Q_g | Total Gate Charge | $V_{GS}=-4.5\text{V}, V_{DS}=-10\text{V}, I_D=-4\text{A}$ | 7.4 | 9.3 | 11 | nC |
| Q_{gs} | Gate Source Charge | | 0.8 | 1 | 1.2 | nC |
| Q_{gd} | Gate Drain Charge | | 1.3 | 2.2 | 3.1 | nC |
| $t_{\text{D(on)}}$ | Turn-On Delay Time | $V_{GS}=-4.5\text{V}, V_{DS}=-10\text{V}, R_L=2.5\Omega, R_{\text{GEN}}=3\Omega$ | | 13 | | ns |
| t_r | Turn-On Rise Time | | | 9 | | ns |
| $t_{\text{D(off)}}$ | Turn-Off Delay Time | | | 19 | | ns |
| t_f | Turn-Off Fall Time | | | 29 | | ns |
| t_{rr} | Body Diode Reverse Recovery Time | $I_F=-4\text{A}, dI/dt=500\text{A}/\mu\text{s}$ | 20 | 26 | 32 | ns |
| Q_{rr} | Body Diode Reverse Recovery Charge | $I_F=-4\text{A}, dI/dt=500\text{A}/\mu\text{s}$ | 40 | 51 | 62 | nC |

A. The value of R_{JJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(\text{MAX})}=150^\circ\text{C}$, using $\leq 10\text{s}$ junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.

D. The R_{JJA} is the sum of the thermal impedance from junction to lead R_{JL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(\text{MAX})}=150^\circ\text{C}$. The SOA curve provides a single pulse rating.



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

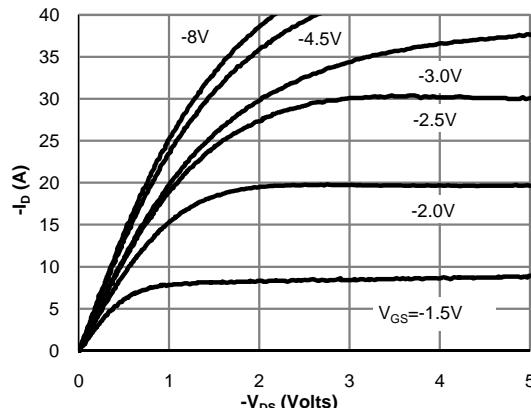


Fig 1: On-Region Characteristics (Note E)

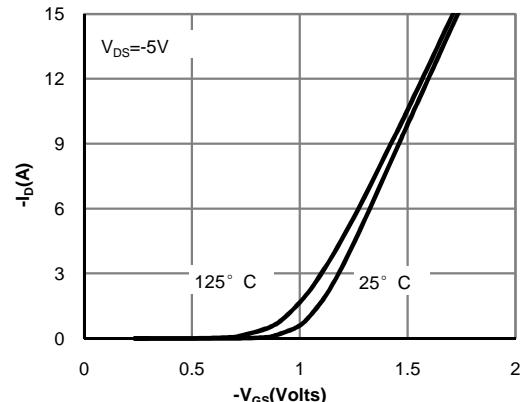


Figure 2: Transfer Characteristics (Note E)

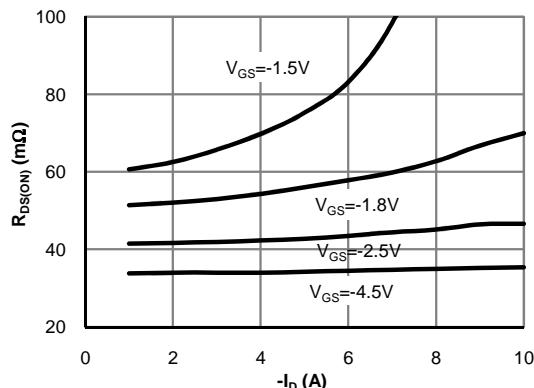


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

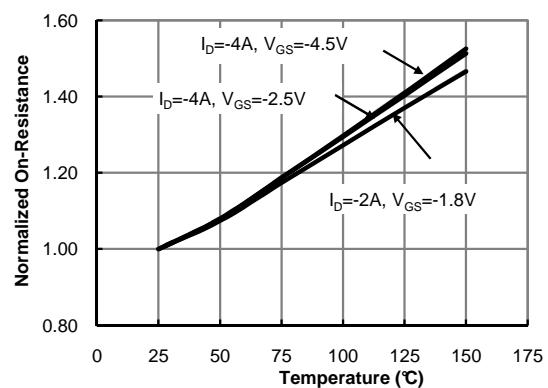


Figure 4: On-Resistance vs. Junction Temperature (Note E)

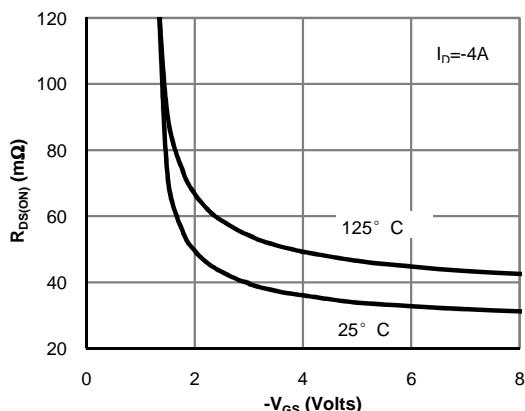


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

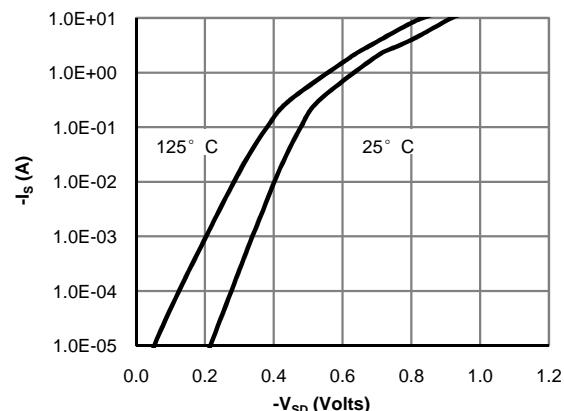


Figure 6: Body-Diode Characteristics (Note E)



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

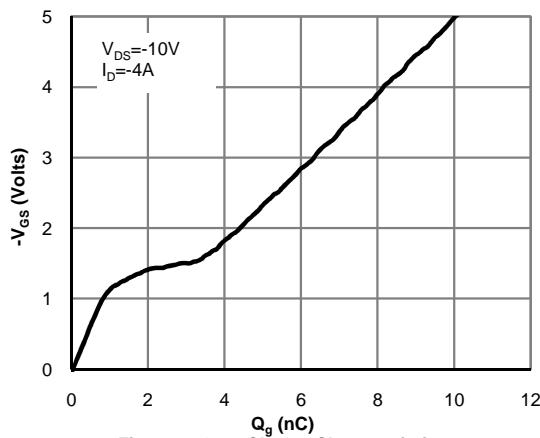


Figure 7: Gate-Charge Characteristics

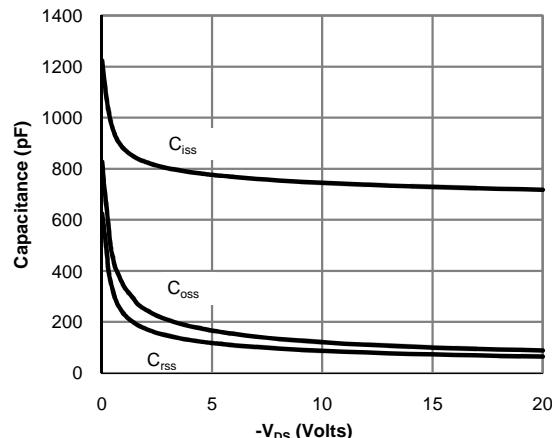


Figure 8: Capacitance Characteristics

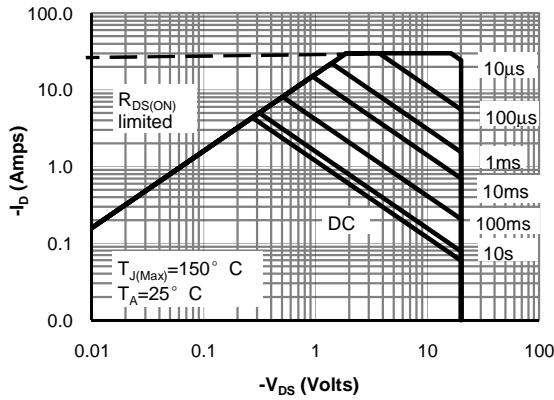


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

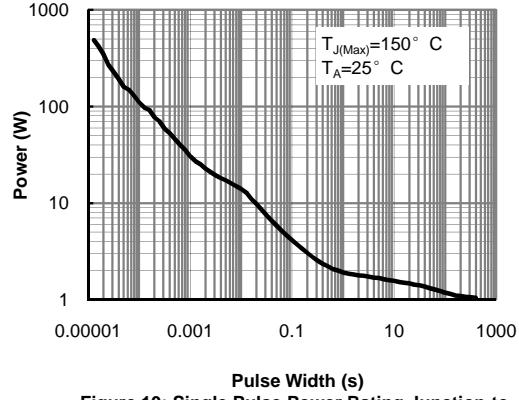


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

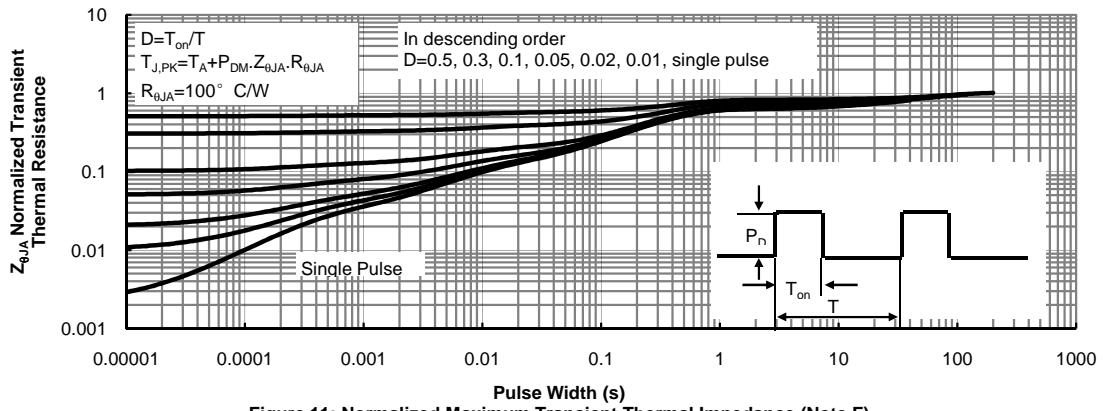
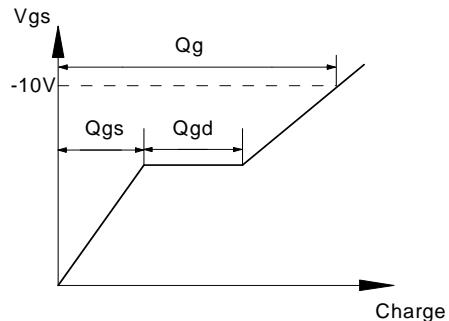
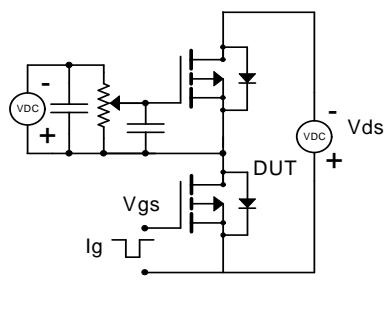


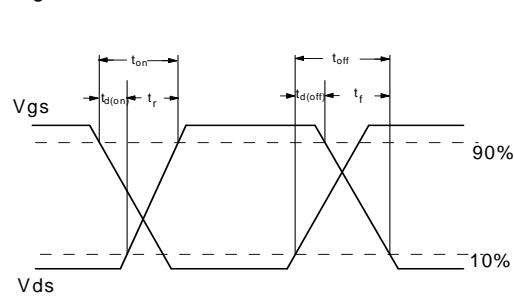
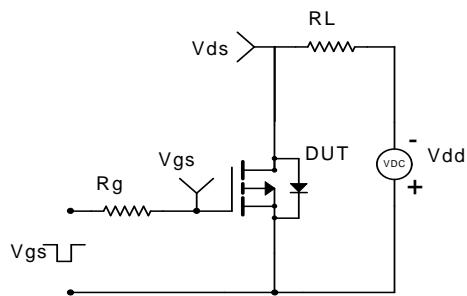
Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)



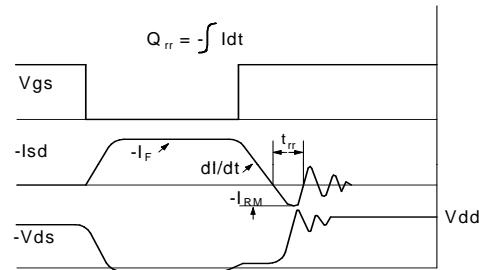
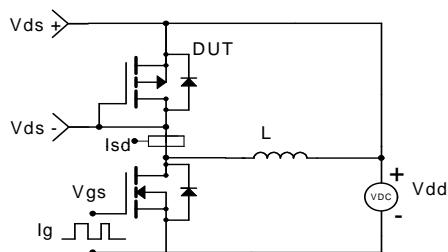
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



| Package | Reel | Reel Size | Box | Box Size(mm) | Carton | Carton Size(mm) |
|---------|---------|-----------|-----------|--------------|------------|-----------------|
| SOT-23 | 3000pcs | 7inch | 45,000pcs | 203×203×195 | 180,000pcs | 438×438×220 |